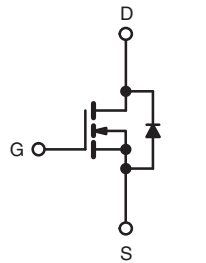
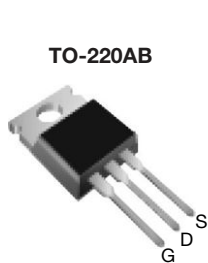


## Power MOSFET

### PRODUCT SUMMARY

$V_{DS}$ (V)	650	
$R_{DS(on)}$ ( $\Omega$ )	$V_{GS} = 10\text{ V}$	0.93
$Q_g$ (Max.) (nC)	48	
$Q_{gs}$ (nC)	12	
$Q_{gd}$ (nC)	19	
Configuration	Single	



N-Channel MOSFET

### FEATURES

- Low Gate Charge  $Q_g$  Results in Simple Drive Requirement
- Improved Gate, Avalanche and Dynamic  $dV/dt$  Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current
- Compliant to RoHS Directive 2002/95/EC


**RoHS\***  
COMPLIANT

### APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply
- High Speed Power Switching

### TYPICAL SMPS TOPOLOGIES

- Single Transistor Flyback
- Single Transistor Forward

### ORDERING INFORMATION

Package	TO-220AB
Lead (Pb)-free	IRFB9N65APbF
	SiHFB9N65A-E3
SnPb	IRFB9N65A
	SiHFB9N65A

### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted)


PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	$V_{DS}$	650	V	
Gate-Source Voltage	$V_{GS}$	$\pm 30$		
Continuous Drain Current	$V_{GS}$ at 10 V	$T_C = 25\text{ }^\circ\text{C}$	A	
		$T_C = 100\text{ }^\circ\text{C}$		
Pulsed Drain Current <sup>a</sup>	$I_{DM}$	21		
Linear Derating Factor		1.3	W/ $^\circ\text{C}$	
Single Pulse Avalanche Energy <sup>b</sup>	$E_{AS}$	325	mJ	
Repetitive Avalanche Current <sup>a</sup>	$I_{AR}$	5.2	A	
Repetitive Avalanche Energy <sup>a</sup>	$E_{AR}$	16	mJ	
Maximum Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	$P_D$	167	W
Peak Diode Recovery $dV/dt^c$	$dV/dt$	2.8	V/ns	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to + 150	$^\circ\text{C}$	
Soldering Recommendations (Peak Temperature)	for 10 s	300 <sup>d</sup>		
Mounting Torque	6-32 or M3 screw	10		lbf · in
		1.1	N · m	

#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Starting  $T_J = 25\text{ }^\circ\text{C}$ ,  $L = 24\text{ mH}$ ,  $R_g = 25\text{ }^\circ\Omega$ ,  $I_{AS} = 5.2\text{ A}$  (see fig. 12).
- $I_{SD} \leq 5.2\text{ A}$ ,  $dI/dt \leq 90\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 150\text{ }^\circ\text{C}$ .
- 1.6 mm from case.

\* Pb containing terminations are not RoHS compliant, exemptions may apply

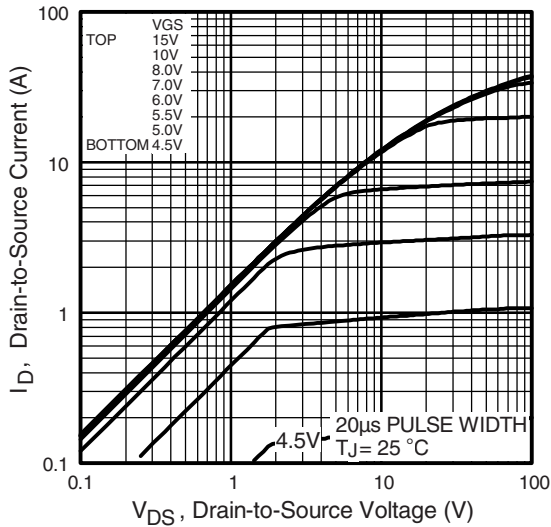
THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	62	°C/W
Case-to-Sink, Flat, Greased Surface	$R_{thCS}$	0.50	-	
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	0.75	

SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
<b>Static</b>							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		650	-	-	V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$ , $I_D = 1\text{ mA}^d$		-	670	-	mV/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2.0	-	4.0	V
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 30\text{ V}$		-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 650\text{ V}, V_{GS} = 0\text{ V}$		-	-	25	$\mu\text{A}$
		$V_{DS} = 520\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 5.1\text{ A}^b$	-	-	0.93	$\Omega$
Forward Transconductance	$g_{fs}$	$V_{DS} = 50\text{ V}, I_D = 3.1\text{ A}$		3.9	-	-	S
<b>Dynamic</b>							
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1.0\text{ MHz}$ , see fig. 5		-	1417	-	pF
Output Capacitance	$C_{oss}$			-	177	-	
Reverse Transfer Capacitance	$C_{rss}$			-	7.0	-	
Output Capacitance	$C_{oss}$	$V_{GS} = 0\text{ V}$	$V_{DS} = 1.0\text{ V}, f = 1.0\text{ MHz}$	-	1912	-	pF
			$V_{DS} = 520\text{ V}, f = 1.0\text{ MHz}$	-	48	-	
Effective Output Capacitance	$C_{oss\text{ eff.}}$	$V_{DS} = 0\text{ V to } 520\text{ V}^c$		-	84	-	
Total Gate Charge	$Q_g$	$V_{GS} = 10\text{ V}$	$I_D = 5.2\text{ A}, V_{DS} = 400\text{ V}$ see fig. 6 and 13 <sup>b</sup>	-	-	48	nC
Gate-Source Charge	$Q_{gs}$			-	-	12	
Gate-Drain Charge	$Q_{gd}$			-	-	19	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 325\text{ V}, I_D = 5.2\text{ A}$ $R_g = 9.1\text{ }\Omega, R_D = 62\text{ }\Omega$ , see fig. 10 <sup>b</sup>		-	14	-	ns
Rise Time	$t_r$			-	20	-	
Turn-Off Delay Time	$t_{d(off)}$			-	34	-	
Fall Time	$t_f$			-	18	-	
<b>Drain-Source Body Diode Characteristics</b>							
Continuous Source-Drain Diode Current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	5.2	A	
Pulsed Diode Forward Current <sup>a</sup>	$I_{SM}$		-	-	21		
Body Diode Voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}, I_S = 5.2\text{ A}, V_{GS} = 0\text{ V}^b$		-	-	1.5	V
Body Diode Reverse Recovery Time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}, I_F = 5.2\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$		-	493	739	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			-	2.1	3.2	$\mu\text{C}$
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$ )					

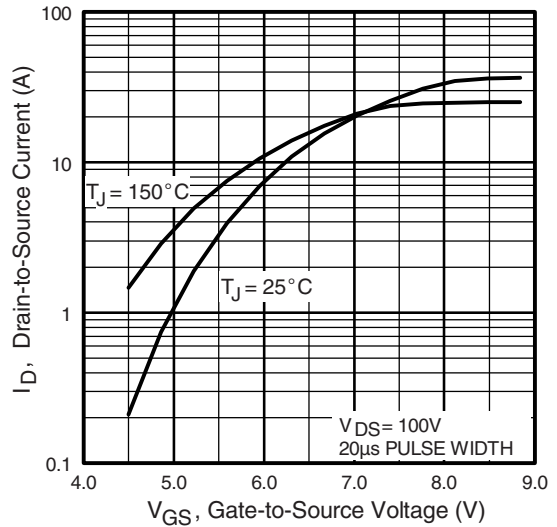
**Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- c.  $C_{oss\text{ eff.}}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DS}$ .
- d. Uses SiHFIB5N65A data and test conditions.

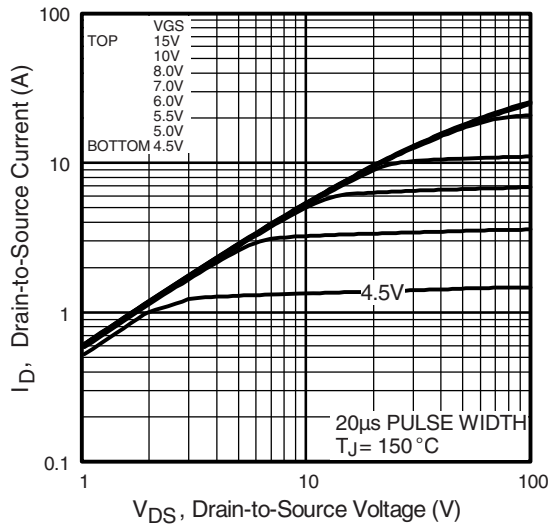
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



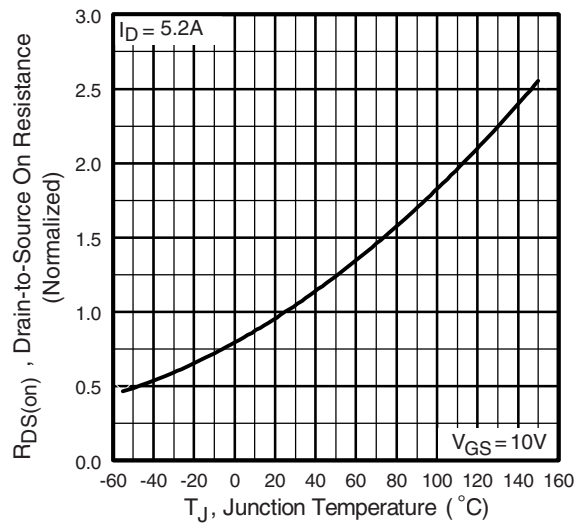
**Fig. 1 - Typical Output Characteristics**



**Fig. 3 - Typical Transfer Characteristics**



**Fig. 2 - Typical Output Characteristics**



**Fig. 4 - Normalized On-Resistance vs. Temperature**

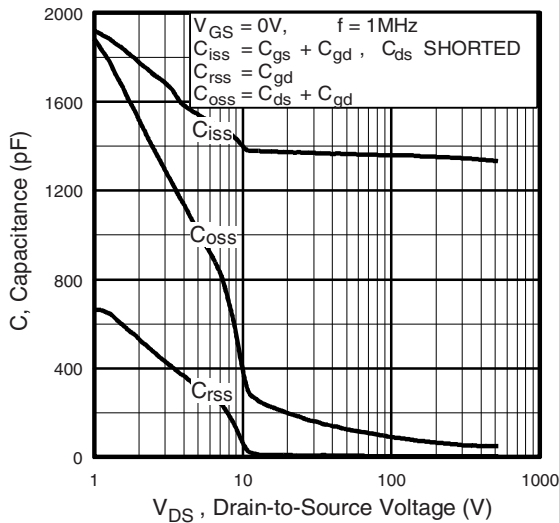


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

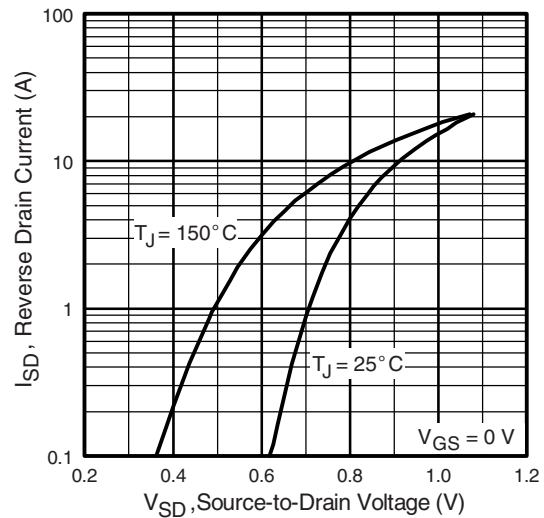


Fig. 7 - Typical Source-Drain Diode Forward Voltage

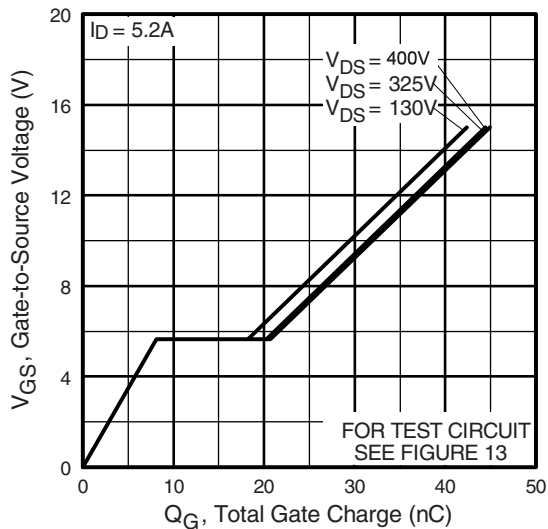


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

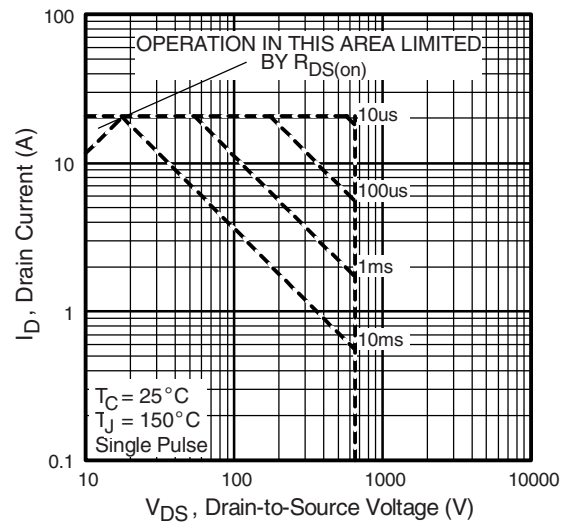


Fig. 8 - Maximum Safe Operating Area

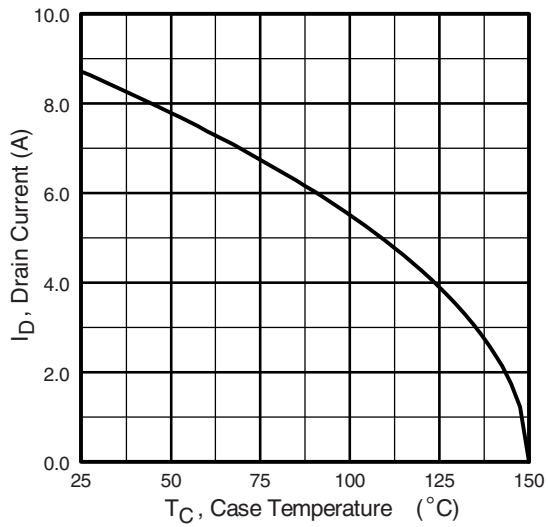


Fig. 9 - Maximum Drain Current vs. Case Temperature

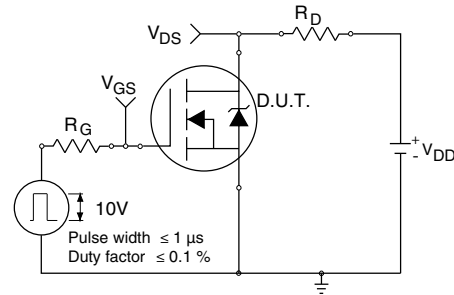


Fig. 10a - Switching Time Test Circuit

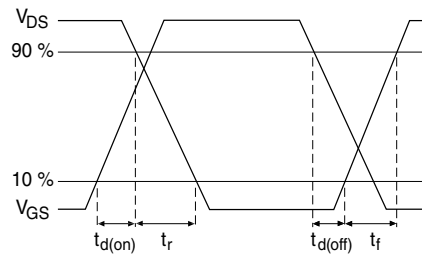


Fig. 10b - Switching Time Waveforms

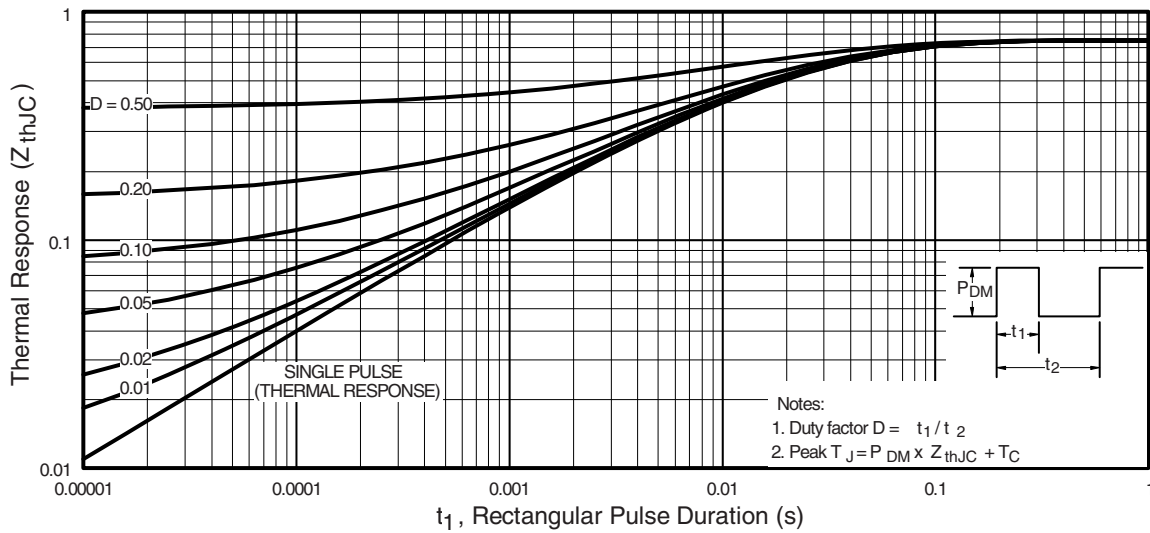
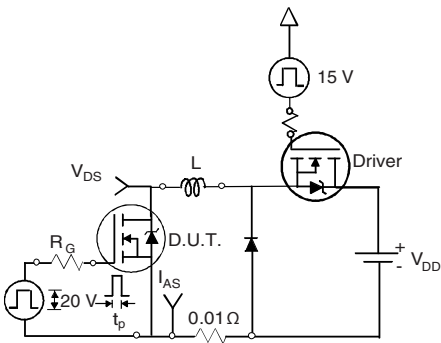
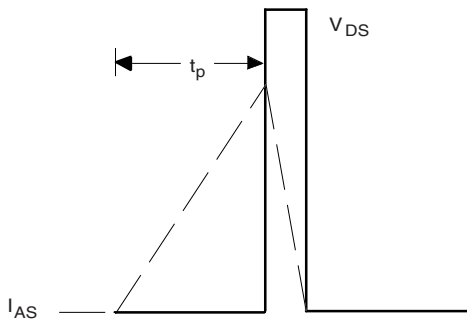


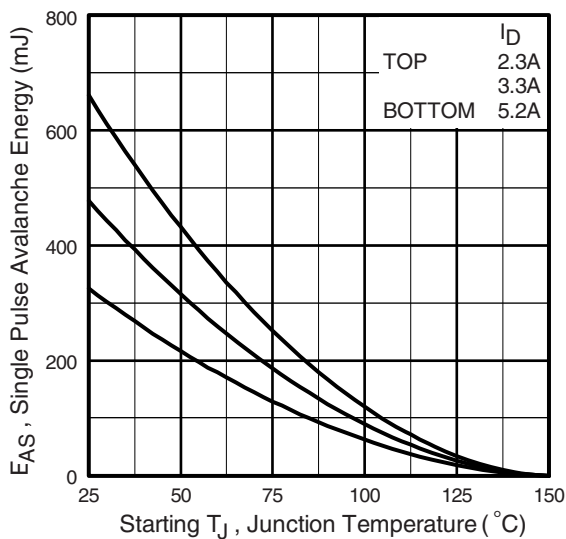
Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case



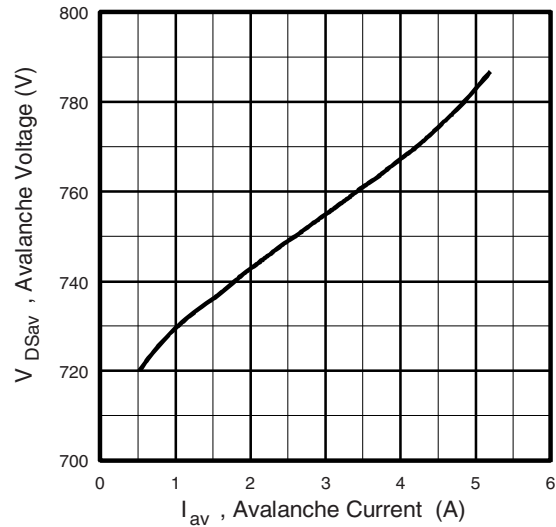
**Fig. 12a - Unclamped Inductive Test Circuit**



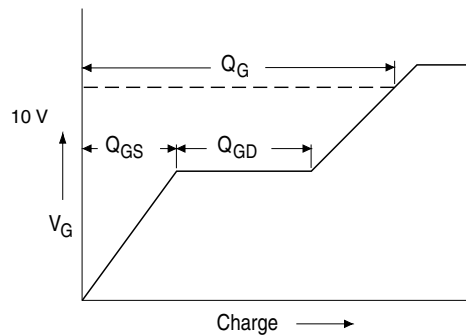
**Fig. 12b - Unclamped Inductive Waveforms**



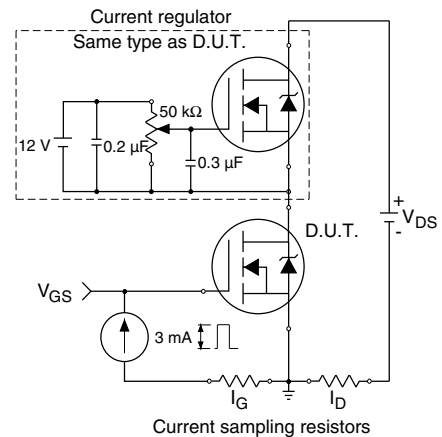
**Fig. 12c - Maximum Avalanche Energy vs. Drain Current**



**Fig. 12d - Typical Drain-to-Source Voltage vs. Avalanche Current**

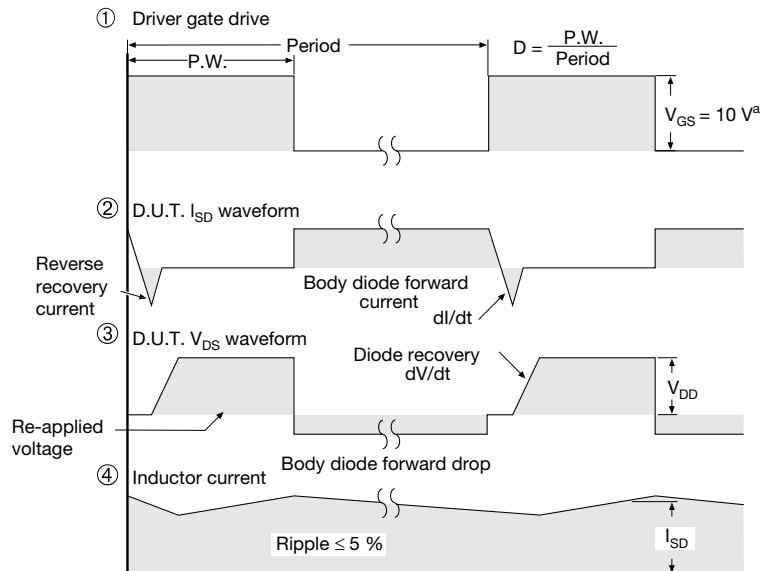
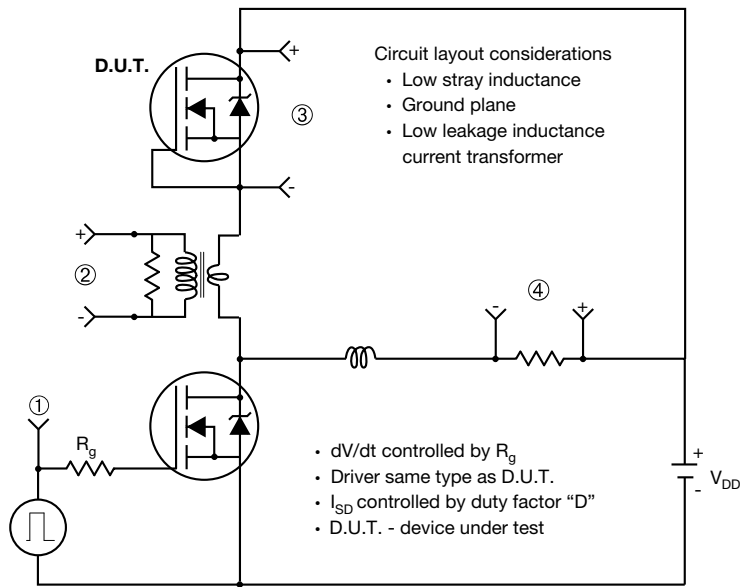


**Fig. 13a - Basic Gate Charge Waveform**



**Fig. 13b - Gate Charge Test Circuit**

### Peak Diode Recovery dV/dt Test Circuit



**Note**

a.  $V_{GS} = 5 V$  for logic level devices

**Fig. 14 - For N-Channel**

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## TO-220-1



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.24	4.65	0.167	0.183
b	0.69	1.02	0.027	0.040
b(1)	1.14	1.78	0.045	0.070
c	0.36	0.61	0.014	0.024
D	14.33	15.85	0.564	0.624
E	9.96	10.52	0.392	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.10	6.71	0.240	0.264
J(1)	2.41	2.92	0.095	0.115
L	13.36	14.40	0.526	0.567
L(1)	3.33	4.04	0.131	0.159
Ø P	3.53	3.94	0.139	0.155
Q	2.54	3.00	0.100	0.118

ECN: X15-0364-Rev. C, 14-Dec-15  
DWG: 6031

**Note**

- M\* = 0.052 inches to 0.064 inches (dimension including protrusion), heatsink hole for HVM







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